

OSRAM SFH 7070

Datasheet

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Tobelbader Strasse 30, 8141 Premstaetten, Austria

Phone +43 3136 500-0

ams-osram.com

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BIOFY®

SFH 7070

Biomonitoring Sensor



Applications

- Health Monitoring (Heart Rate Monitoring, Pulse Oximetry)

Features

- ESD: 2 kV acc. to ANSI/ESDA/JEDEC JS-001 (HBM, Class 2)
- Multi chip package featuring two green emitters and one detector
- Package size: (WxDxH) 7.5 mm x 3.9 mm x 0.9 mm
- Light Barrier to block optical crosstalk
- optimized for strong PPG signal

Ordering Information

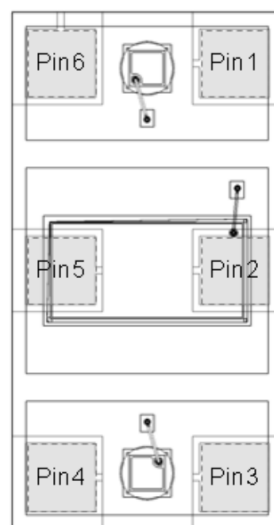
Type
SFH 7070

Ordering Code
Q65111A9887

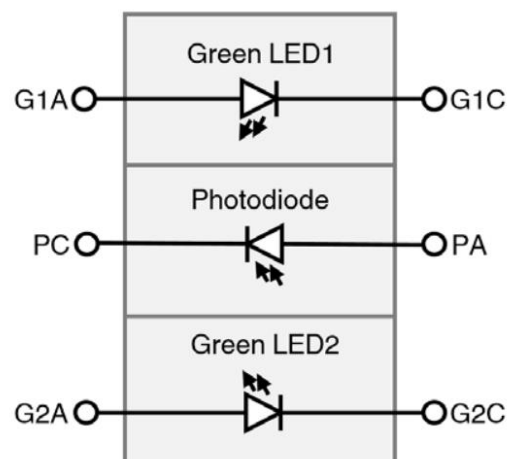
Pin configuration

Pin	Name	Function
1	Green 1	Green LED 1 Cathode
2	PD	Photodiode Anode
3	Green 2	Green LED 2 Cathode
4	Green 2	Green LED 2 Anode
5	PD	Photodiode Cathode
6	Green 1	Green LED 1 Anode

Top view



Block diagramm



Maximum Ratings

$T_A = 25\text{ °C}$

Parameter	Symbol	Values	
Operating temperature range	T_{op}	min.	-40 °C
		max.	85 °C
Storage temperature range	T_{stg}	min.	-40 °C
		max.	85 °C
ESD withstand voltage acc. to ANSI/ESDA/JEDEC JS-001 - HBM	V_{ESD}	max.	2 kV
Green Emitters			
Reverse voltage ⁵⁾	V_R	max.	5 V
Forward current	$I_F (DC)$	max.	25 mA
Forward current pulsed $t_p = 5\text{ ms}$, $D = 0.005$	$I_F \text{ pulse}$	max.	300 mA
Photodiode			
Reverse voltage	V_R	max.	16 V

Characteristics

$T_A = 25\text{ °C}$

Parameter	Symbol		Values
Green Emitter (single emitter)			
Peak wavelength I _F = 20 mA	λ _{peak}	typ.	526 nm
Centroid Wavelength ⁶⁾ I _F = 20 mA	λ _{centroid}	min. typ. max.	520 nm 530 nm 540 nm
Spectral bandwidth at 50% of I _{max} I _F = 20 mA	Δ λ	typ.	32 nm
Half angle	φ	typ.	± 60 °
Rise time (10% and 90%) I _F = 100 mA, t _p = 16 μs, R _L = 50 Ω	t _r	typ.	60 ns
Fall time (10% and 90%) I _F = 100 mA, t _p = 16 μs, R _L = 50 Ω	t _f	typ.	60 ns
Forward voltage ⁷⁾ I _F = 20 mA	V _F	typ. max.	2.4 V 2.8 V
Reverse current V _R = 5 V	I _R	.	Not designed for reverse operation
Radiant intensity I _F = 20 mA, t _p = 20 ms	I _e	typ.	4.8 mW / sr
Total radiant flux I _F = 20 mA, t _p = 20 ms	Φ _e	typ.	15 mW
Temperature coefficient of brightness I _F = 20 mA, t _p = 20 ms	TC _I	typ.	-0.35 % / K
Temperature coefficient of wavelength I _F = 20 mA, t _p = 20 ms	TC _λ	typ.	0.03 nm / K
Temperature coefficient of voltage I _F = 20 mA, t _p = 20 ms	TC _V	typ.	-3.6 mV / K

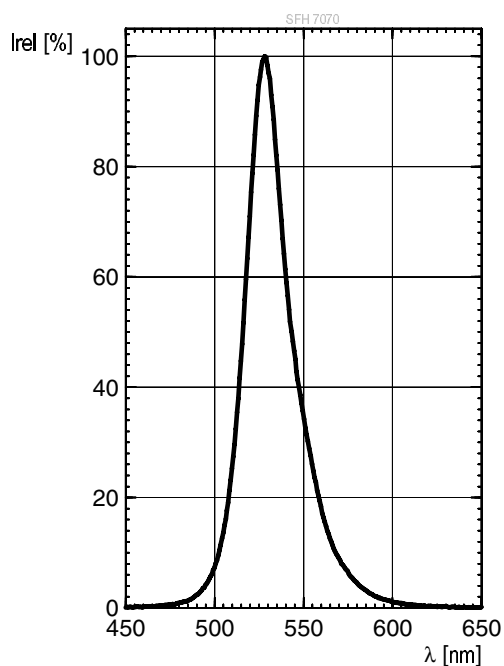
Characteristics

 $T_A = 25\text{ °C}$

Parameter	Symbol		Values
Photodiode			
Wavelength of max. sensitivity	$\lambda_{S\ max}$	typ.	635 nm
Spectral range of sensitivity	$\lambda_{10\%}$	typ.	402 ... 694 nm
Photocurrent $E_e = 0.1\ \text{mW/cm}^2$, $\lambda = 530\ \text{nm}$, $V_R = 5\ \text{V}$	I_P	typ.	0.985 μA
Radiation sensitive area	A	typ.	3.46 mm ²
Dimensions of radiant sensitive area	$L \times W$	typ.	1.29 x 2.69 mm x mm
Half angle	ϕ	typ.	$\pm\ 57^\circ$
Dark current $V_R = 5\ \text{V}$, $E_e = 0\ \text{mW/cm}^2$	I_R	typ. max.	0.4 nA 5 nA
Spectral sensitivity of the chip $\lambda = 530\ \text{nm}$	S_λ	typ.	0.31 A / W
Spectral sensitivity of the chip $\lambda \geq 690\ \text{nm}$	S_{IR}	typ.	0.02 A / W
Open-circuit voltage $E_e = 0.1\ \text{mW/cm}^2$, $\lambda = 530\ \text{nm}$	V_O	typ.	390 mV
Short-circuit current $E_e = 0.1\ \text{mW/cm}^2$, $\lambda = 530\ \text{nm}$	I_{SC}	typ.	0.984 μA
Rise time $V_R = 5\ \text{V}$, $R_L = 50\ \Omega$, $\lambda = 530\ \text{nm}$	t_r	typ.	40 ns
Fall time $V_R = 5\ \text{V}$, $R_L = 50\ \Omega$, $\lambda = 530\ \text{nm}$	t_f	typ.	40 ns
Forward voltage $I_F = 10\ \text{mA}$, $E = 0\ \text{mW/cm}^2$	V_F	typ.	0.84 V
Capacitance $V_R = 5\ \text{V}$, $f = 1\ \text{MHz}$, $E = 0\ \text{mW/cm}^2$	C_0	typ.	55 pF

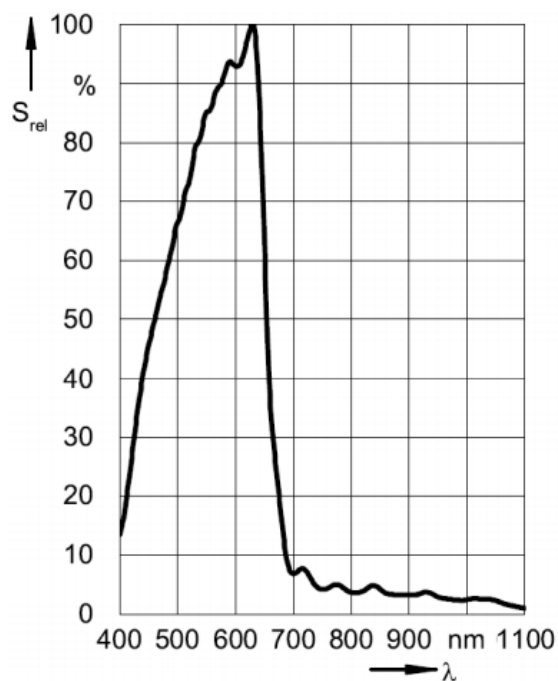
Relative Spectral Emission ^{1), 2)}

- true green: $I_{e,rel} = f(\lambda)$; $I_F = 20 \text{ mA}$; $t_p = 20 \text{ ms}$



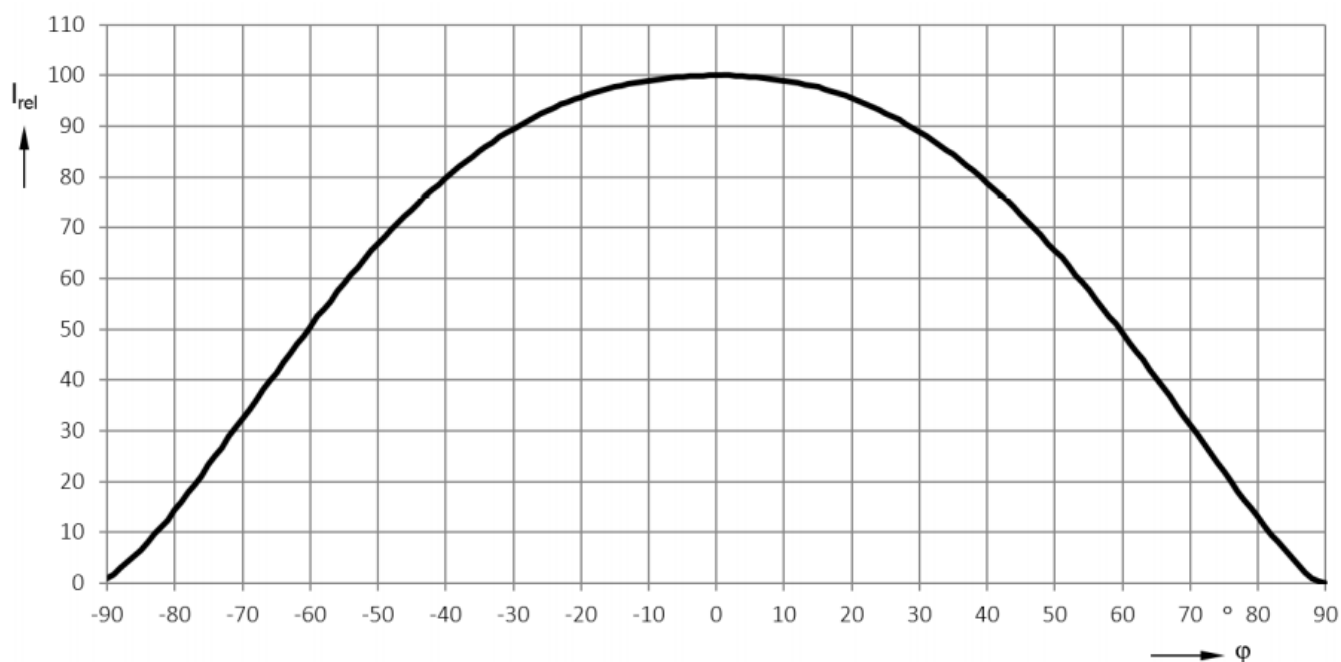
Relative Spectral Sensitivity ^{1), 2)}

- photodiode: $S_{rel} = f(\lambda)$



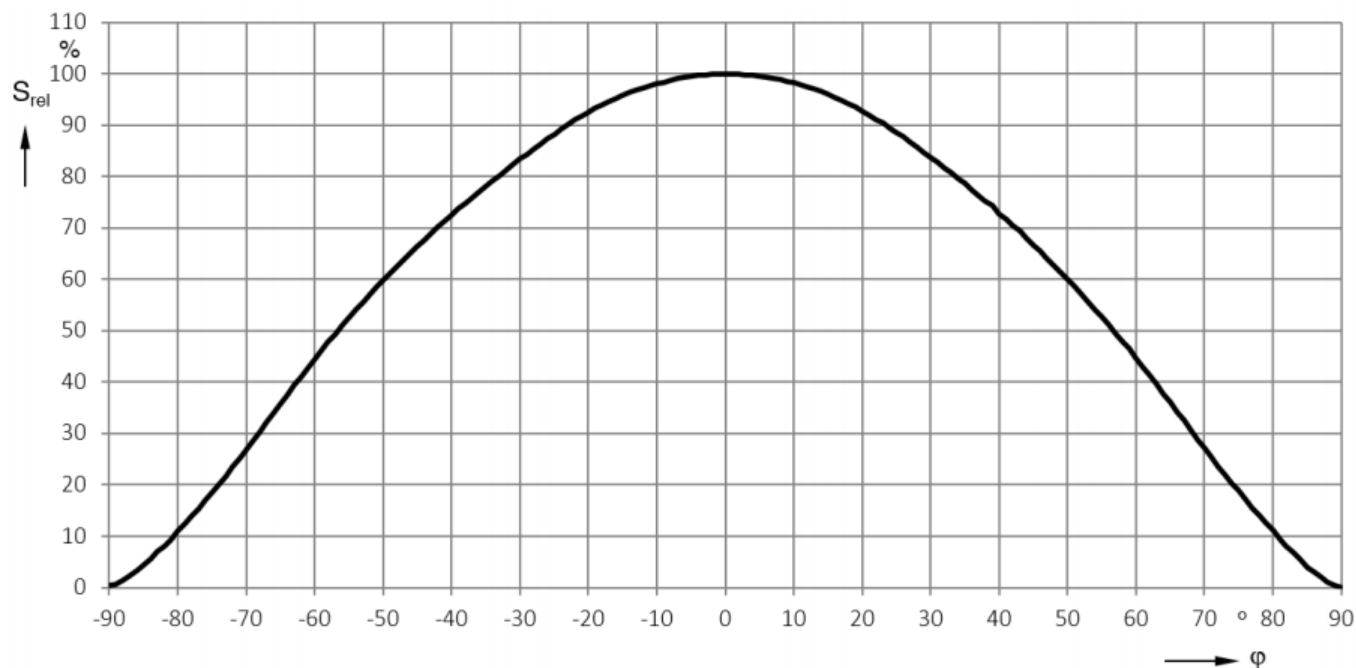
Radiation Characteristics ^{1), 2)}

- true green: $I_{e,rel} = f(\varphi)$



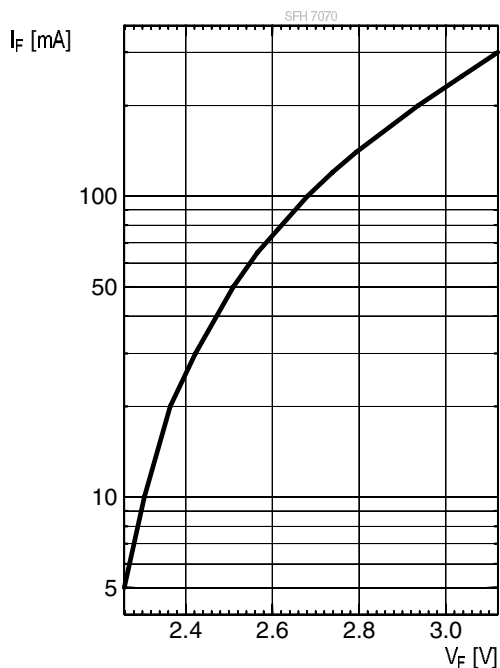
Directional Characteristics ^{1), 2)}

- photodiode: $S_{rel} = f(\lambda)$; $\lambda = 530\text{nm}$



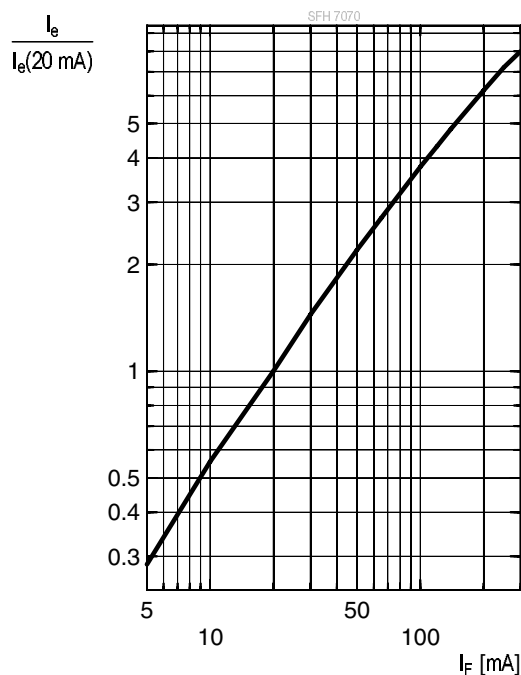
Forward current ^{1), 2)}

- true green: $I_F = f(V_F)$; single pulse; $t_p = 100 \mu s$



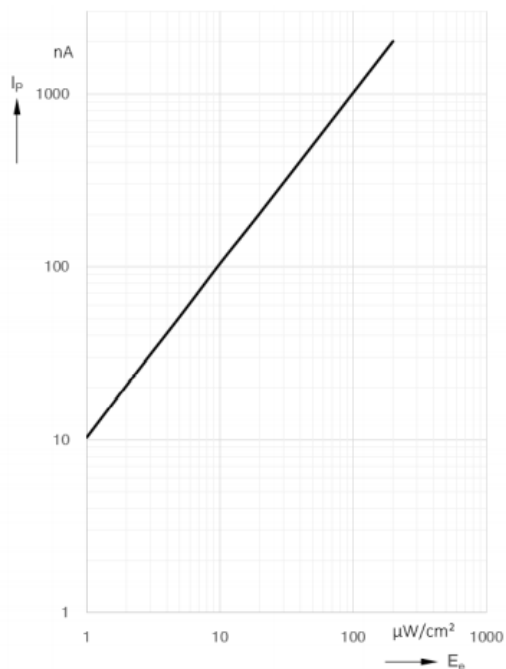
Relative Radiant Intensity ^{1), 2)}

- true green: $I_e/I_e(20mA) = f(I_F)$; single pulse; $t_p = 25 \mu s$



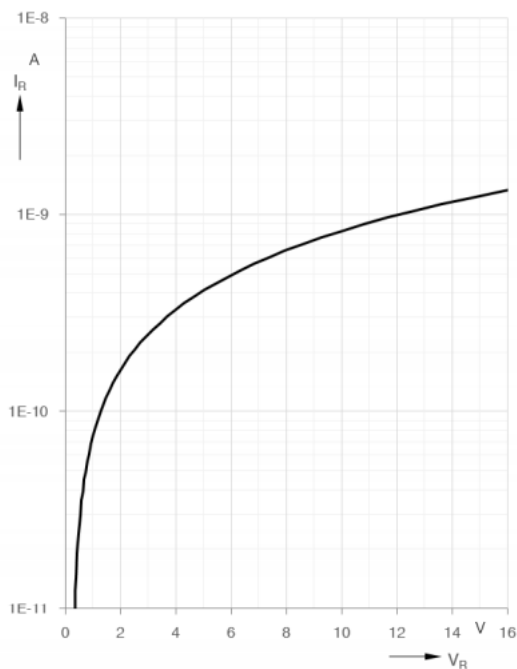
Photocurrent ^{1), 2)}

- photodiode: $I_P = f(E_e)$; $\lambda = 530 \text{ nm}$; $V_R = 5 \text{ V}$



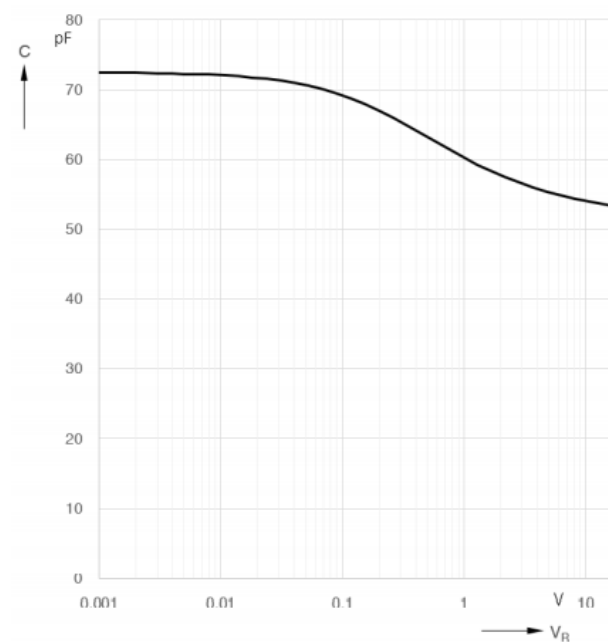
Dark Current ^{1), 2)}

- photodiode: $I_R = f(V_R)$; $E = 0$

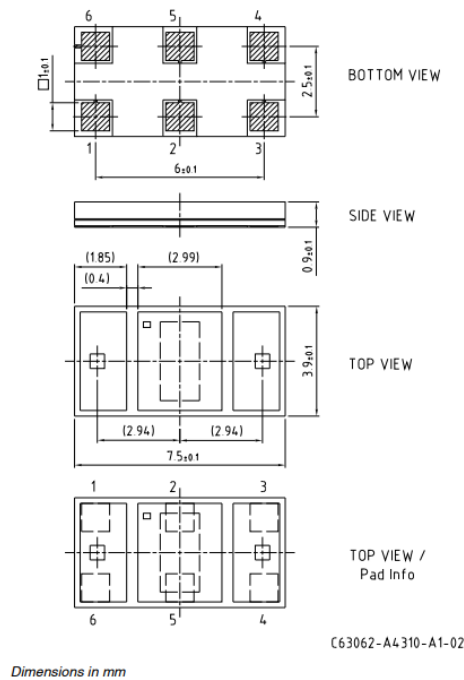


Capacitance ^{1), 2)}

■ photodiode: $C = f(V_R)$; $f = 1\text{MHz}$; $E = 0$



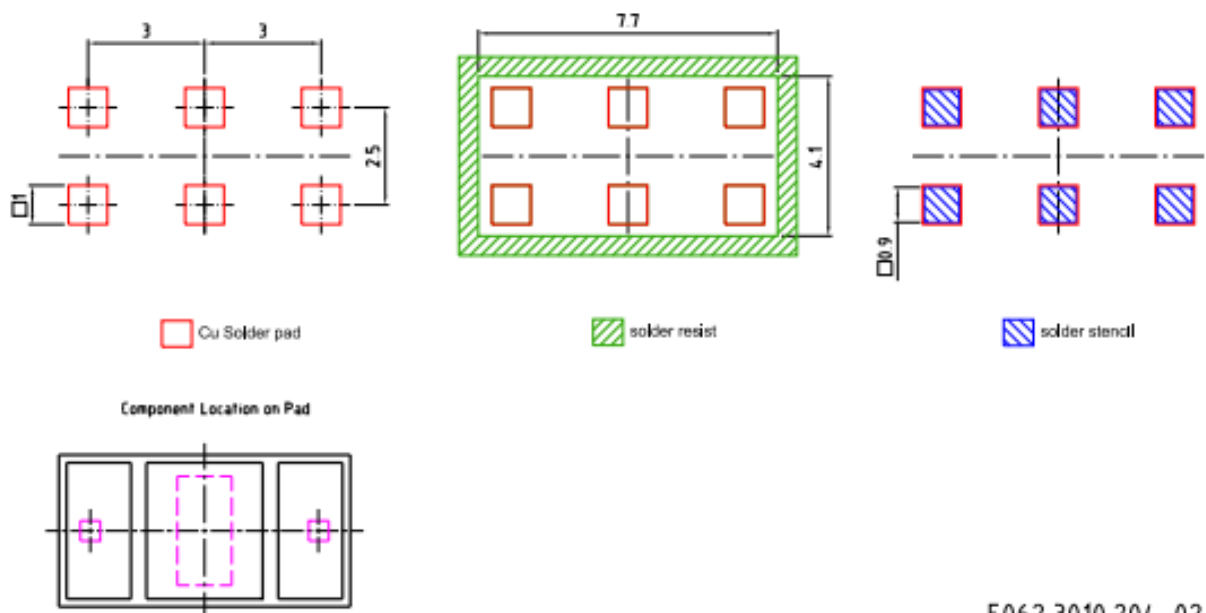
Dimensional Drawing ³⁾



Further Information:

Approximate Weight: 44.0 mg

Recommended Solder Pad ³⁾

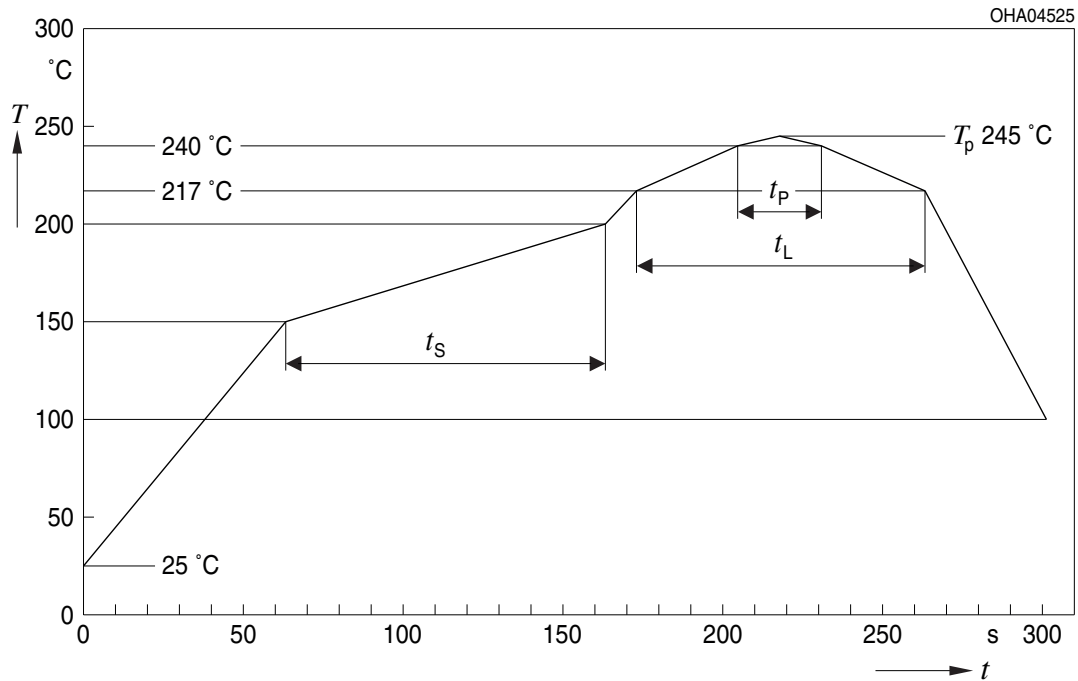


Dimensions in mm (inch).

E062.3010.204-02

Reflow Soldering Profile

Product complies to MSL Level 4 acc. to JEDEC J-STD-020E

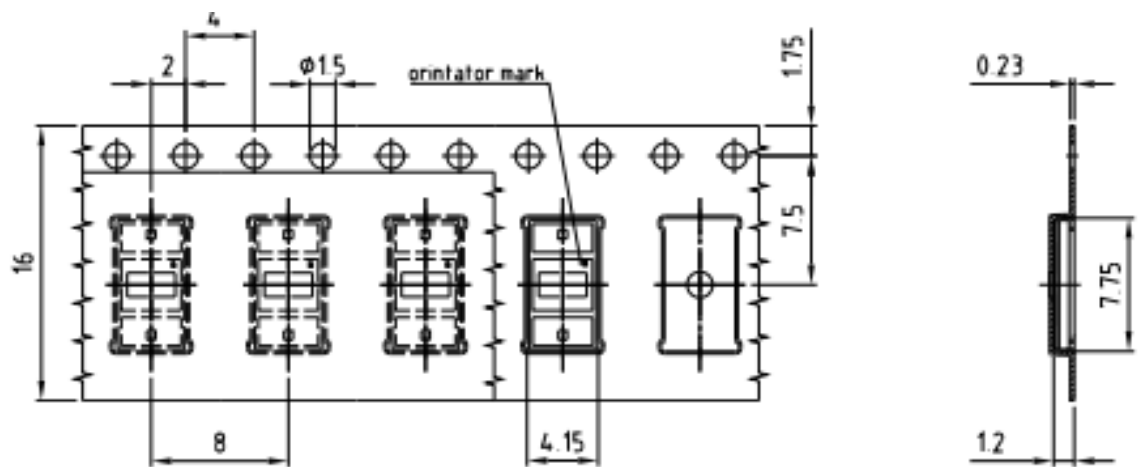


Profile Feature	Symbol	Pb-Free (SnAgCu) Assembly			Unit
		Minimum	Recommendation	Maximum	
Ramp-up rate to preheat ^{*)} 25 °C to 150 °C			2	3	K/s
Time t_s T_{Smin} to T_{Smax}	t_s	60	100	120	s
Ramp-up rate to peak ^{*)} T_{Smax} to T_p			2	3	K/s
Liquidus temperature	T_L		217		$^{\circ}\text{C}$
Time above liquidus temperature	t_L		80	100	s
Peak temperature	T_p		245	260	$^{\circ}\text{C}$
Time within 5 °C of the specified peak temperature $T_p - 5\text{ K}$	t_p	10	20	30	s
Ramp-down rate* T_p to 100 °C			3	6	K/s
Time 25 °C to T_p				480	s

All temperatures refer to the center of the package, measured on the top of the component

* slope calculation DT/Dt : Dt max. 5 s; fulfillment for the whole T-range

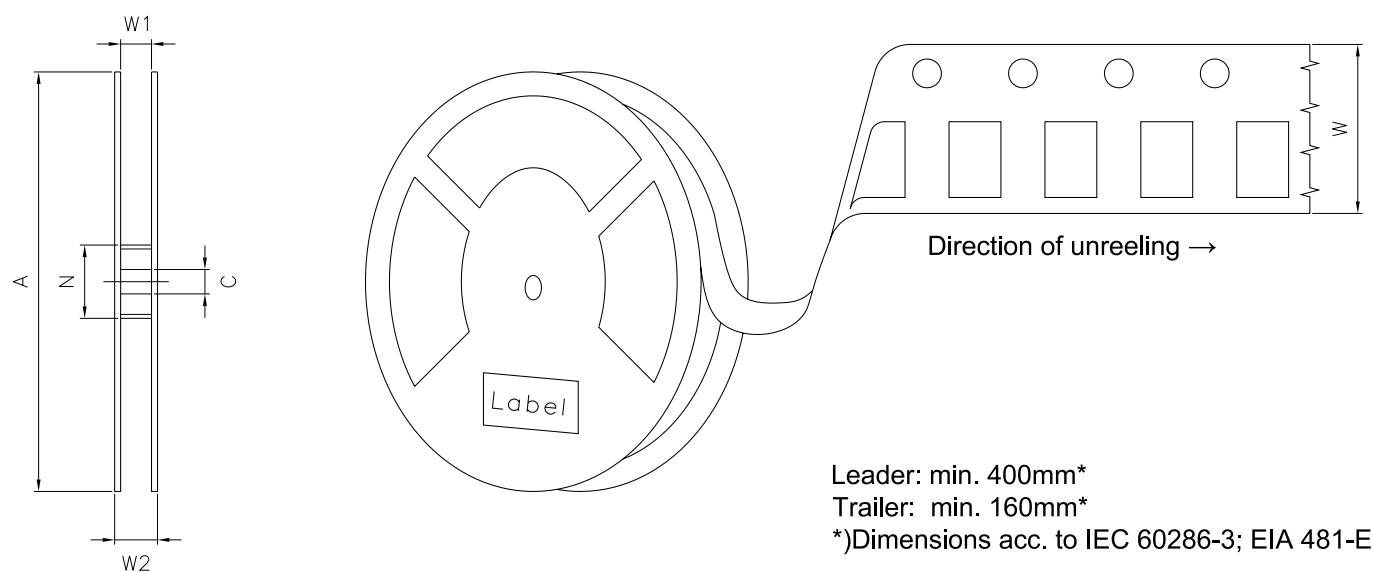
Taping ³⁾



C63062-A4310-B2 -02

Dimensions in mm [inch].

Tape and Reel ⁴⁾



Reel Dimensions

A	W	N _{min}	W ₁	W _{2 max}	Pieces per PU
180 mm	16 + 0.3 / - 0.1 mm	60/100 mm	16.4 + 2 mm	22.4 mm	1500

OSRAM Opto Semiconductors		LX XXXX	BIN1: XX-XX-X-XXX-X
(6P) BATCH NO: 1234567890		RoHS Compliant	
		ML Temp ST X XXX °C X	
(1T) LOT NO: 1234567890	(9D) D/C: 1234	Pack: RXX DEMY XXX X_X123_1234.1234 X	
(X) PROD NO: 123456789	(Q) QTY: 9999	(G) GROUP: XX-XX-X-X	

Dry Packing Process and Materials ³⁾



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Disclaimer

Attention please!

The information describes the type of component and shall not be considered as assured characteristics. Terms of delivery and rights to change design reserved. Due to technical requirements components may contain dangerous substances.

For information on the types in question please contact our Sales Organization.

If printed or downloaded, please find the latest version on our website.

Packing

Please use the recycling operators known to you. We can also help you – get in touch with your nearest sales office. By agreement we will take packing material back, if it is sorted. You must bear the costs of transport. For packing material that is returned to us unsorted or which we are not obliged to accept, we shall have to invoice you for any costs incurred.

Product and functional safety devices/applications or medical devices/applications

Our components are not developed, constructed or tested for the application as safety relevant component or for the application in medical devices.

Our products are not qualified at module and system level for such application.

In case buyer – or customer supplied by buyer – considers using our components in product safety devices/ applications or medical devices/applications, buyer and/or customer has to inform our local sales partner immediately and we and buyer and /or customer will analyze and coordinate the customer-specific request between us and buyer and/or customer.

Glossary

- 1) **Typical Values:** Due to the special conditions of the manufacturing processes of semiconductor devices, the typical data or calculated correlations of technical parameters can only reflect statistical figures. These do not necessarily correspond to the actual parameters of each single product, which could differ from the typical data and calculated correlations or the typical characteristic line. If requested, e.g. because of technical improvements, these typ. data will be changed without any further notice.
- 2) **Testing temperature:** $T_A = 25^{\circ}\text{C}$ (unless otherwise specified)
- 3) **Tolerance of Measure:** Unless otherwise noted in drawing, tolerances are specified with ± 0.1 and dimensions are specified in mm.
- 4) **Tape and Reel:** All dimensions and tolerances are specified acc. IEC 60286-3 and specified in mm.
- 5) **Reverse Operation:** This product is intended to be operated applying a forward current within the specified range. Applying any continuous reverse bias or forward bias below the voltage range of light emission shall be avoided because it may cause migration which can change the electro-optical characteristics or damage the LED.
- 6) **Wavelength:** The wavelengths are measured with a tolerance of ± 1 nm.
- 7) **Forward Voltage:** The forward voltages are measured with a tolerance of ± 0.1 V.

Revision History

Version	Date	Change
1.2	2021-04-27	New Layout
1.3	2022-05-10	Characteristics Electro - Optical Characteristics (Diagrams) New Layout



EU RoHS and China RoHS compliant product

此产品符合欧盟 RoHS 指令的要求；
按照中国的相关法规和标准，
不含有毒有害物质或元素。

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